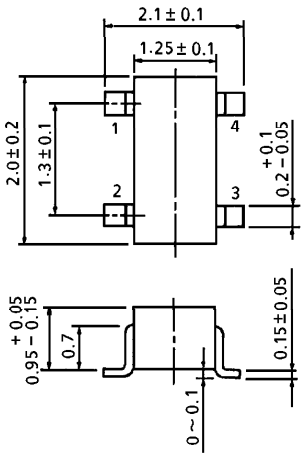
TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

1SV312

VHF~UHF BAND RF ATTENUATOR APPLICATIONS

Unit in mm



1. ANODE 1
2. ANODE 2
3. CATHODE 2
4. CATHODE 1

USQ	
JEDEC	—
EIAJ	—
TOSHIBA	1-2U1A

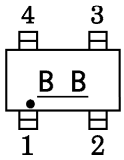
Weight : 0.006 g

- Two independent diodes mounted onto a 4-pin ultra compact package and it is suitable for high-density circuit design.
- Low Capacitance : C_T = 0.25 pF (Typ.)
- Low Series Resistance : r_s = 3 Ω (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATIN	UNIT
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX	UNIT
Reverse Voltage	V_R	I_R = 10 μA	50	—	—	V
Reverse Current	I_R	V_R = 50 V	—	—	0.1	μA
Forward Voltage	V_F	I_F = 50 mA	—	0.95	1	V
Total Capacitance	C_T	V_R = 50 V, f = 1 MHz	—	0.25	0.4	pF
Series Resistance	r_s	I_F = 10 mA, f = 100 MHz	—	3	—	Ω

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